



## INFORMATIONDISCLOSURE CITATION PADE

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et	Number (Opt	ional)

December 19, 2001

12318-US

Application Number

10/021,081

2878

Dan-xia	Xu	et	al.

Annlicant(s) Filing Date

Group Art Unit

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIAT
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Form PTO-A820 (also form PTO-1449)

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Patent and Trademark Office \* U.S. DEPARTMENT OF COMMERCE

INFORMATIONDISCLOSURECITATION

Docket Number (Optional) 12318-US	Application Number 10/021,081
Applicant(s)	

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(Use several sheets if necessary)				Dan-xia xu et al.				
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